Paper / Subject Code: 42501 / Embedded System Design

Total Marks: 80

(Time:3 Hours)

2) Attempt any three questions from remaining five questions.

Note: 1) Question No.1 is compulsory.

3)	-	suitable data if necessary.	
		to the right indicate full marks.	
-/	8		
Q.1)	Explain	in brief	
C /	-	EDLC	5M
	a)		0,00
	b)	SPI	5M
	c)	Semaphores	5M
	d)	Task states	5M
Q.2)	a)	What is the necessity of task scheduling? Explain Task Switching.	10M
		Three periodic processes scheduled using EDF, will processes meet the deadlines?	NA ST
		Process Execution Time = e _i Period = p _i	
		P1 1 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8	33
		P2 2 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	7
	1 \	P3 4 10 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	103.5
	b)	Suggest the various strategies to help faster programming.	10M
Q.3)	a)	What is priority inheritance problem? Explain it with neat sketch. Suggest	10M
		solutions.	
	b)	What need is of debug and trace facility? How cortex M3 supports it?	10M
.			403.5
Q.4)	a)	Design G+ n an elevator system. Give the proper details for this,	10M
		i. FSM which describes the functioning of the system	
		ii. Hardware block diagram and list of components with justification	
		iii. Design challenges and suggest solutions for ethical practice in	
		development	
b) Explain various design metrics. Explain the various optimization challenges			
		for embedded system.	
Q.5)	a) (What are different communications means available for industrial field	10M
i.S	3,000	devices?	
66	(b)	Explain briefly register structure of Cortex M3 architecture along with the	10M
VA 50	00 6 16 16 16 16 16 16 16 16 16 16 16 16 1	function of various special registers.	
06		Give the companies and details between block how and white how testing	10 N /I
Q.6)	a)	Give the comparison details between black box and white box testing.	10M
\$30°	b) _	Write short note on: i)Various data types ii)FPGA	10M
36 F	7.82 S	XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	

(3 Hours) [Total Marks: 80]

- **N. B.:** (1) Question No. 1 is compulsory.
 - (2) Attempt any **THREE** questions from the remaining five questions.
 - (3) Assume suitable data if necessary.
 - (4) Figures to the right indicate full marks.

Q1. Attempt any four questions.

20

- a) What problems will be faced if thyristors are used in an inverter circuit?
- b) State true or false with justification: Buck-boost converters are difficult to model and control.
- c) Explain the process of torque generation in a DC motor.
- d) An induction motor basically works on the principle of Lenz's Law. Explain the meaning of this statement.
- e) What are SMPS? Explain any SMPS circuit with the help of neat waveforms.
- Q2. a) Compare with the help derivation, the output DC voltage of a single-phase fully controlled bridge rectifier with and without source inductance. Can it be concluded that source inductance is an undesired factor in the performance of a controlled rectifier?

10

- b) In a 3- Φ full converter working in rectifier mode, input supply is 440V (L-L) 50 Hz AC. If firing angle $\alpha = \Pi/4$ and load current is 20A constant with load voltage = 370V, determine source inductance Ls and overlap angle μ .
- Q3. a) Derive and explain the average state space model of Buck Converter. Use this state space model to derive equation for output voltage of the converter at equilibrium condition (dv/dt=0).
- b) Explain various feedback control methods for DC-DC converters. Which method is best suitable for efficient control? Which method does not require mathematical model of the converter?

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		5/49 (27/97)
Q4. a) Giv	ven a single phase AC supply, design a power electronic circuit to	charge a
battery. Ho	w will you decide the current requirement of the circuit?	10
b) List t	the desirable features of an UPS. Explain on line and off line UPS.	10
from single	20V, 1500 rpm, 10 A separately excited DC motor has Ra=2 Ω at a phase fully controlled bridge rectifier with source voltage of 230V continuous load current, compute:	2 20 20 AY
Assuming C	continuous load current, compute:	
(i) Motor s	speed at firing angle of 45 degrees and torque of 4 N-m.	
(ii) Develop	ped torque at firing angle of 30 degrees and speed of 1200 rpm.	
b) Exp	plain the variable frequency control method for speed control of in	nduction
motor for tv	wo different working modes.	10
Q6. Write s	short notes on (any two)	20
i)	Importance of output filter in an inverter.	
ii)	Advantages of SVM over conventional sine wave PWM.	
iii)	Modeling of DC-DC converter.	
iv)	Induction heating.	

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(3 hours)		Marks: 80
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Note: 1) Question No. 1 is compulsory.

- 2) Out of remaining questions, attempt any 3 questions.
- 3) In all 4 questions to be attempted.
- 4) All questions carry equal marks.
- 5) Figures in brackets on the right hand side indicate full marks.
- 6) Assume Suitable data if necessary
- Q.1 Answer any Four of the following.
 - a. Chain codes can be made invariant to rotation. Justify. [5]
 - b. Briefly explain fundamental steps in image processing. [5]
 - c. Briefly explain image enhancement in frequency domain. [5]
 - d. List different types of data redundancies present in Digital Image. Explain [5] them.
 - e. The principal function of median filter is to force points with distinct intensities [5] to be more like neighbours. State TRUE or FALSE and Justify.
- Q.2. a. Given below 5×5 image. Operate on the central 3×3 pixels by low pass and high pass masks and obtain 3×3 images as output. [10]

6	5.0	12	12	3
14	12	13	10	9
10	15	40	10	6
8	3.	7	40	7.8
8	3	10	8	5

Using these outputs verify

Original Image=Low Pass Output + High Pass Output

In case of discrepancy explain the reason.

- b. Explain any three point processing techniques with the help of transformation [10] graphs.
- Q.3. a. Perform histogram equalization and plot the histogram before and after [10] equalization.

(//	6	4	3	0	7
1/2	2	$\mathcal{T}_{\mathbb{C}}$	5	3	0
3	4	2	7	0	7
7 1	1	5	4	0	6
) [4	7	5	4	1

b. A source emits four symbols (a,b,c,d) with the probabilities 0.4, 0.2, 0.1, and 0.3 respectively. Construct arithmetic coding to encode and decode the word "cab".

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- Q.4. a. How edges are detected in digital image using gradient and Laplace operators. [10]
 - b. Explain following methods of image segmentation by giving appropriate [10] illustrations: (i) region growing (ii) Splitting and merging.
- Q.5. a. For a 2x2 transform **A** and the image **U**, Compute the transformed image **V**, and [10] the basis image. Also reconstruct the original image **U** from the transformed image **V**.

$$A = \frac{1}{\sqrt{2}} \begin{bmatrix} 1 & 1 \\ 1 & -1 \end{bmatrix} \quad \text{and} \quad U = \begin{bmatrix} 1 & 2 \\ 3 & 4 \end{bmatrix}$$

b. Apply Fast Hadamard algorithm to the rows and columns of the 2-D image segment shown below. Show the butterfly diagrams. [10]

$\overline{0}$	15	2	1
	2	3	2
2	3	4	3
16	2	3	2

- Q.6. Write short notes on (any Four)
 - a. Homomorphic Filtering. [5]
 - b. Opening and Closing. [5]
 - c. Colour Models. [5]
 - d. Region Filling [5]
 - e. Image Compression Models. [5]

Paper / Subject Code: 42502 / IC Technology

N.B. 1) Question No.1 is compulsory 2) Solve any three questions from the remaining questions. 3) Assume suitable data if necessary. 1. Answer any four: (a) Describe bonded SOI and smart cut SOI method (b) Enlist the steps for obtaining Si from sand. (c) What is short channel effect? How to avoid it? (d) Explain any one application of nanowire (e) Explain difference between positive and negative photo resist 2. (a) Explain Liquid phase epitaxy method. What are its advantage and disadvantage? (b) Explain RCA cleaning method. (c) State comparison of APCVD, LPCVD and PECVD. 3. (a) Enlist step for fabrication of CMOS inverter using N well process. Draw vertical cross sectional view starting from substrate till the gate, source and drain formation in fabrication of CMOS inverter. (b) Draw layout of 2 input CMOS NAND gate using lambda based design rule 4 (a)Describe with help of neat diagram of Hyness schokley experiment for measurement of drift mobility of n type semiconductor (b) Explain Deal and Groove model for oxidation (c) Explain BiCMOS 5 (a)What is LOCOS? Why it is required in CMOS process. Explain technology solution for avoiding problem in LOCOS. (b) Explain Difference between Schottky contact and ohmic contact (c) Explain Difference between Dry etching and Wet etching 6 Write short notes (a) MODFET devices (b) Multigate device structure (c) High k and low k dielectric (d) Need of lambda based design rule (e) X ray lithography		(3 Hours) Total Marks:	80
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	Time: 3 Hours	Marks: 80
	Note before:	
	1) Question no. 1 is compulsory	
	2) Attempt any three from the remaining questions	
	3) Assume suitable data wherever necessary	
Q.1.	Answer any FOUR:	20
	a) Explain various LAN topologies with neat diagrar	$\tilde{\mathbf{n}}$
	b) What is meant by the terms bit stuffing and byte s	tuffing?
	c) Write a note on Bellman Ford Algorithm.	
	d) Explain ALOHA and slotted ALOHA.	
	e) An ISP is granted a block of addresses starting with	
	120.60.4.0/22. The ISP wants to distribute this blo	
	organizations with 8 addresses each. Design sub b	
	give the slash notations for each sub block. Find h	
	addresses are still available after these allocations.	
	f) Compare connection oriented and connection less	services
	with examples	
Q.2.a.	Write a note on sliding window protocol.	10
b.	Explain the function of MAC and LLC sub layers.	10
Q.3.a.	Draw and explain IPv4 header. Compare IPv4 and IPv6.	10
b.	Write a short note on ICMP.	10
Q.4.a.	Describe three way handshake in TCP. Why do we have	it only in 10
Q. 4 .a.	TCP and not in UDP.	t Omy iii 10
b.	Explain how TCP handles error control and flow control?	10
Q.5.a.	State and explain various types of frames in HDLC.	10
b.	Explain OSI and TCP/IP and explain the function of each	a layer. 10
Q.6.	Write short note on (any two):	20
13.0	a)Berkley API	
	b) CSMA/CD and CSMA/CA	
	c) Domain Name Server	
	\$`\Z.`O.'\D.`&_O.\\$\'\&\'\\$\'\\$\\\\\\\\\\\\\\\\\\\\\\\\\	